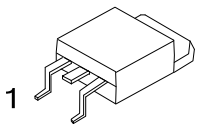
2N70-CA

Power MOSFET

2A, 700V N-CHANNEL POWER MOSFET



TO-252

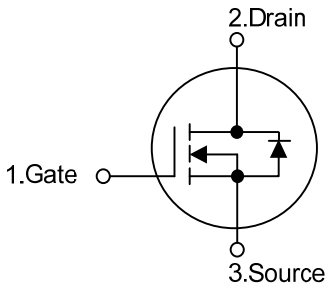
■ DESCRIPTION

The UTC **2N70-CA** is a high voltage MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

■ FEATURES

* $R_{DS(ON)}$ < 5.2Ω @ V_{GS} = 10V , I_D = 1.0 A
* Fast switching capability
* Avalanche energy specified
* Improved dv/dt capability, high ruggedness

■ SYMBOL



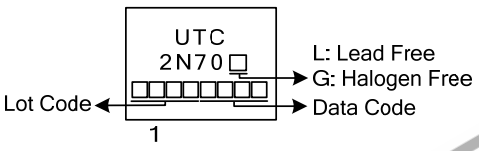
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2N70L-TN3-R	2N70G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

2N70L-TN3-R (1) Packing Type (2) Package Type (3) Green Package	(1) R: Tape Reel (2) TN3: TO-252 (3) L: Lead Free, G: Halogen Free and Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	700	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	Continuous	I_D	2.0	A
	Pulsed (Note 2)	I_{DM}	8.0	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	100	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation		P_D	30	W
Junction Temperature		T_J	+150	°C
Operating Temperature		T_{OPR}	-55 ~ +150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating : Pulse width limited by T_J.
3. L=40mH, I_{AS}=2.0A, V_{DD}=50V, R_G=25 Ω, Starting T_J = 25°C
4. I_{SD}≤2.0A, di/dt≤200A/μs, V_{DD}≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL RESISTANCES CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	110	°C/W
Junction to Case	θ_{JC}	4.24	°C/W

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS} = 0V, I_D = 250μA	700			V
Drain-Source Leakage Current		I_{DSS}	V_{DS} = 700V, V_{GS} = 0V			10	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS} = 30V, V_{DS} = 0V			100	nA
	Reverse		V_{GS} = -30V, V_{DS} = 0V			-100	nA
Breakdown Voltage Temperature Coefficient		$\triangle BV_{DSS}/\triangle T_J$	I_D = 250 μA, Referenced to 25°C		0.4		V/°C
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS} = V_{GS}, I_D = 250μA	3.0		5.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS} = 10V, I_D =1.0A			5.2	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C_{ISS}	V_{DS} =25V, V_{GS} =0V, f =1MHz		240		pF
Output Capacitance		C_{OSS}			37		pF
Reverse Transfer Capacitance		C_{RSS}			3.7		pF
SWITCHING CHARACTERISTICS							
Turn-On Delay Time		$t_{D\ (ON)}$	V_{DD}=30V, I_D =0.5A, R_G =25Ω (Note 1, 2)		40		ns
Turn-On Rise Time		t_R			24		ns
Turn-Off Delay Time		$t_{D(OFF)}$			65		ns
Turn-Off Fall Time		t_F			19		ns
Total Gate Charge		Q_G	V_{DS}=50V, I_D=1.3A, V_{GS}=10V (Note 1, 2)		12		nC
Gate-Source Charge		Q_{GS}			4.7		nC
Gate-Drain Charge		Q_{GD}			1.8		nC
DRAIN-SOURCE DIODE CHARACTERISTICS							
Drain-Source Diode Forward Voltage		V_{SD}	V_{GS} = 0 V, I_{SD} = 2.0 A			1.4	V
Continuous Drain-Source Current		I_{SD}				2.0	A
Pulsed Drain-Source Current		I_{SM}				8.0	A
Body Diode Reverse Recovery Time		t_{RR}	I_S=2.0A, dI/dt=100A/μs		300		nS
Body Diode Reverse Recovery Charge		Q_{RR}			1.3		nC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle≤2%
2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

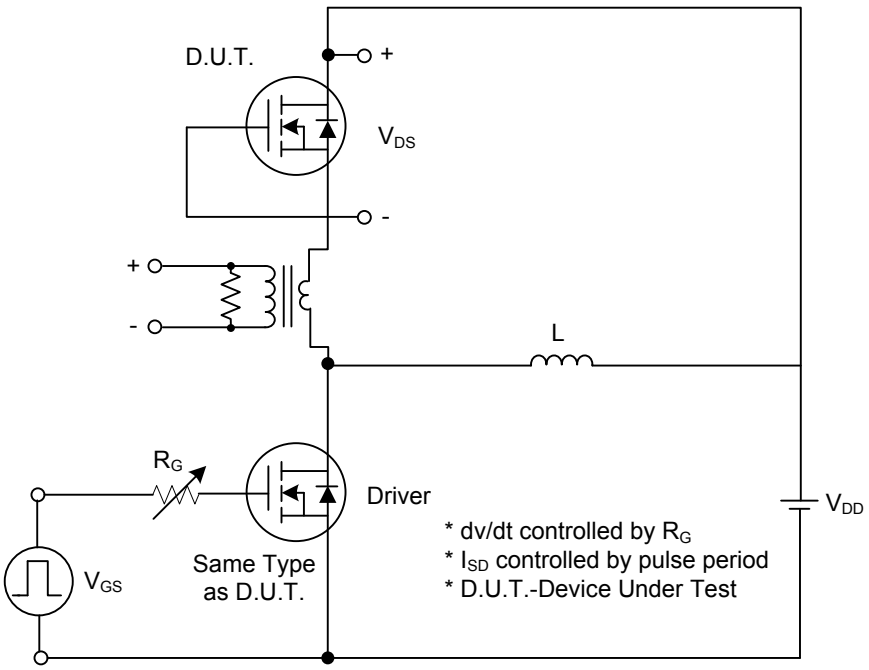


Fig. 1A Peak Diode Recovery dv/dt Test Circuit

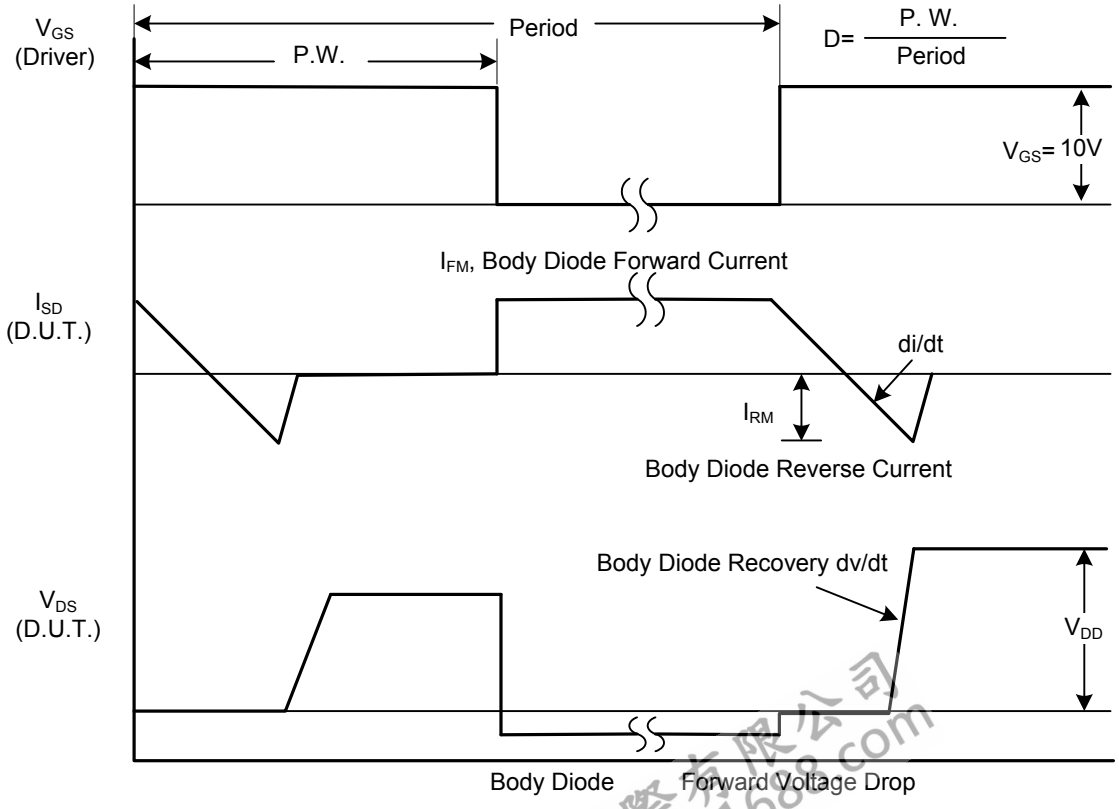


Fig. 1B Peak Diode Recovery dv/dt Waveforms

■ TEST CIRCUITS AND WAVEFORMS (Cont.)

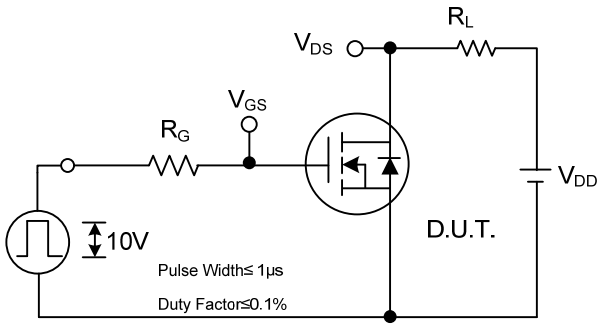


Fig. 2A Switching Test Circuit

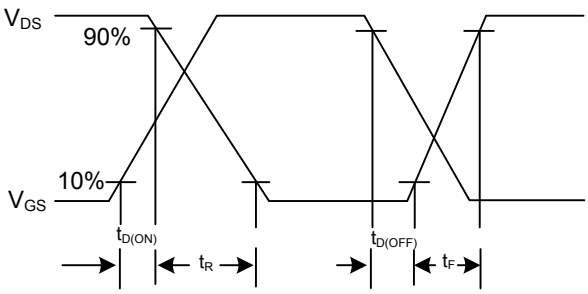


Fig. 2B Switching Waveforms

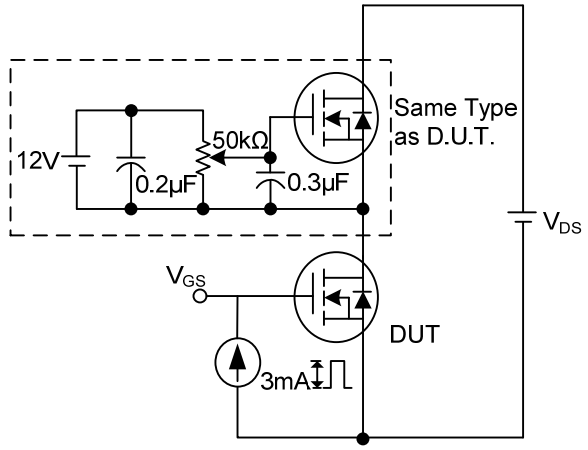


Fig. 3A Gate Charge Test Circuit

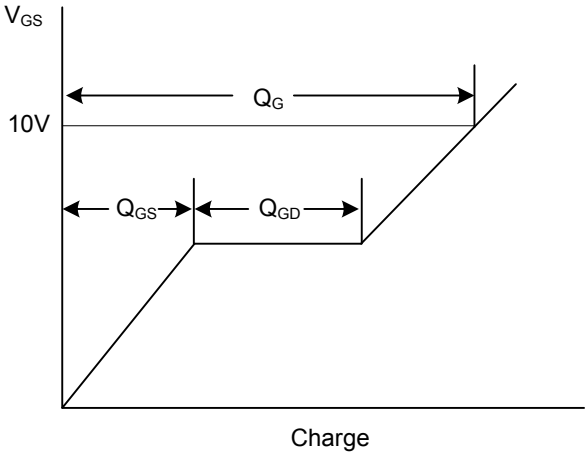


Fig. 3B Gate Charge Waveform

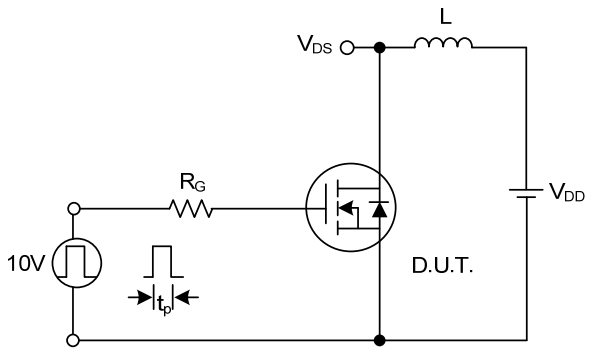


Fig. 4A Unclamped Inductive Switching Test Circuit

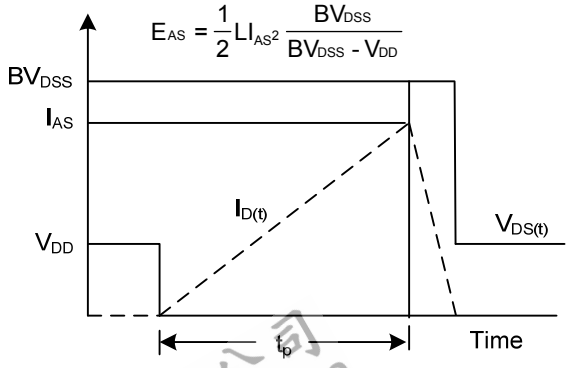
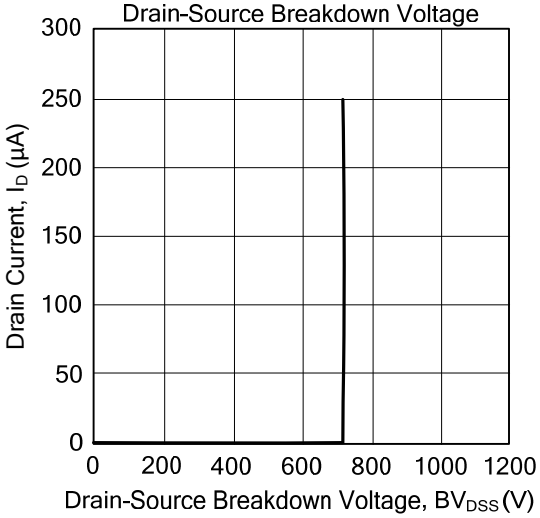


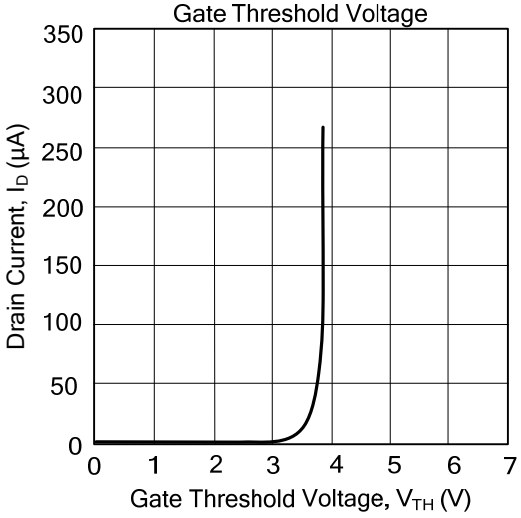
Fig. 4B Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

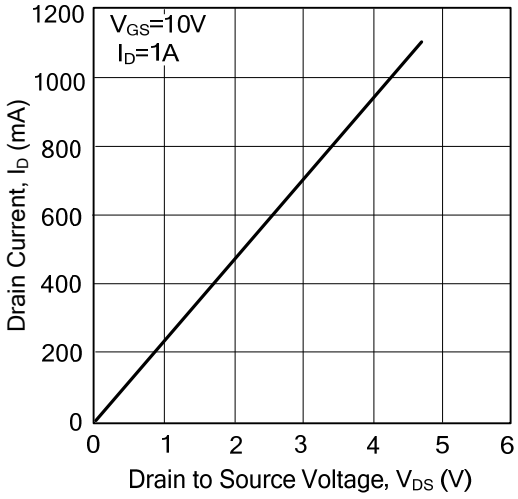
Drain Current vs.
Drain-Source Breakdown Voltage



Drain Current vs.
Gate Threshold Voltage



Drain-Source vs.
On-State Resistance Characteristics



Continuous Drain-Source Current vs.
Source to Drain Voltage